International Rectifier

PD - 9.1250

Provisional

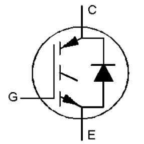
IRGPH40KD2

INSULATED GATE BIPOLAR TRANSISTOR
WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast CoPack IGBT

Features

- Short circuit - 10µs @ 125°C, V_{GE} = 10V
- Short circuit - 5µs @ 125°C, V_{GE} = 15V
- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for high operating frequency (over 5kHz) See Fig. 1 for Current vs. Frequency curve



n-channel

V_{CES} = 1200V

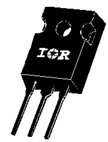
$V_{CE(sat)} \leq$ 4.5V

@V_{GE} = 15V, I_C = 10A

Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.


TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current	18	A
I_C @ T_C = 100°C	Continuous Collector Current	10	
I_{CM}	Pulsed Collector Current ①	36	
I_{LM}	Clamped Inductive Load Current ②	36	
I_F @ T_C = 100°C	Diode Continuous Forward Current	8.0	
I_{FM}	Diode Maximum Forward Current	36	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	160	W
P_D @ T_C = 100°C	Maximum Power Dissipation	65	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	——	——	0.77	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	——	——	1.7	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	——	.24	——	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	——	——	40	
Wt	Weight	——	6 (0.21)	——	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	1200	—	—	V	V_{GE} = 0V, I_C = 250μA
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.97	—	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.8	3.5	V	I_C = 10A; V_{GE} = 15V, See Fig. 2, 5
		—	3.6	—		I_C = 18A
		—	2.9	—		I_C = 10A, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		V_{CE} = V_{GE}, I_C = 250μA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V_{CE} = V_{GE}, I_C = 250μA
g_{fe}	Forward Transconductance ④	2.2	6.5	—	S	V_{CE} = 100V, I_C = 10A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V_{GE} = 0V, V_{CE} = 1200V
		—	—	3500		V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C
V_{RM}	Diode Forward Voltage Drop	—	2.6	3.3	V	I_C = 8.0A; See Fig. 13
		—	2.3	3.0		I_C = 8.0A, T_J = 125°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	50	75	nC	I_C = 10A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	13	20		V_{CC} = 400V
Q_{gc}	Gate - Collector Charge (turn-on)	—	14	21		See Fig. 8
$t_{d(on)}$	Turn-On Delay Time	—	51	—	ns	I_C = 10A, V_{CC} = 800V
t_r	Rise Time	—	26	—		V_{GE} = 15V, R_G = 10Ω
$t_{d(off)}$	Turn-Off Delay Time	—	62	93		Energy losses include "tail" and
t_f	Fall Time	—	330	640		diode reverse recovery.
E_{on}	Turn-On Switching Loss	—	1.0	—	mJ	See Fig. 9, 10, 11, 18
E_{off}	Turn-Off Switching Loss	—	1.2	—		
E_{ts}	Total Switching Loss	—	2.2	3.4		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	V_{GE} = 10V; V_{CC} = 720V, T_J = 125°C
		5.0	—	—		V_{GE} = 15V; R_G = 10Ω, V_{CPK} < 1000V
$t_{d(on)}$	Turn-On Delay Time	—	51	—	ns	T_J = 150°C, See Fig. 9, 10, 11, 18
t_r	Rise Time	—	28	—		I_C = 10A, V_{CC} = 800V
$t_{d(off)}$	Turn-Off Delay Time	—	190	—		V_{GE} = 15V, R_G = 10Ω
t_f	Fall Time	—	550	—		Energy losses include "tail" and
E_{ts}	Total Switching Loss	—	3.6	—	mJ	diode reverse recovery.
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	1400	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	100	—		V_{CC} = 30V; See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	15	—		f = 1.0MHz
t_{rr}	Diode Peak Reverse Recovery Time	—	63	95	ns	T_J = 25°C; See Fig. 14; I_F = 8.0A, V_R = 200V, di/dt = 200A/μs
		—	106	160		T_J = 125°C
I_{rr}	Diode Peak Reverse Recovery Current	—	4.5	8.0	A	T_J = 25°C; See Fig. 15
		—	6.2	11		T_J = 125°C
Q_{rr}	Diode Reverse Recovery Charge	—	140	380	nC	T_J = 25°C; See Fig. 16
		—	335	880		T_J = 125°C
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	133	—	A/μs	T_J = 25°C; See Fig. 17
		—	85	—		T_J = 125°C

Notes:

① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (See fig. 20)

② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = 10μH, R_G = 10Ω, (See fig. 19)

③ Pulse width ≤ 80μs; duty factor ≤ 0.1%.

④ Pulse width 5.0μs, single shot.

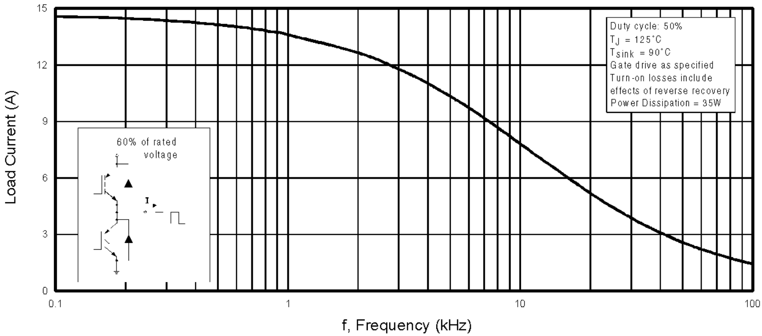


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

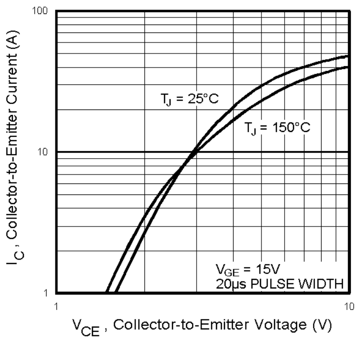


Fig. 2 - Typical Output Characteristics

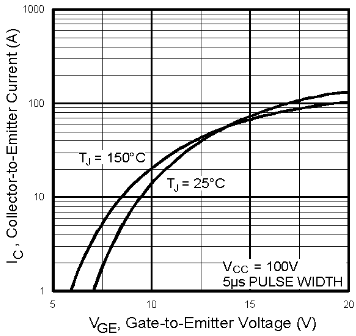


Fig. 3 - Typical Transfer Characteristics

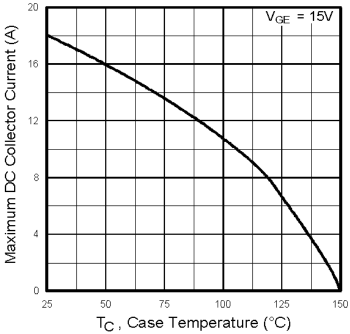


Fig. 4 - Maximum Collector Current vs. Case Temperature

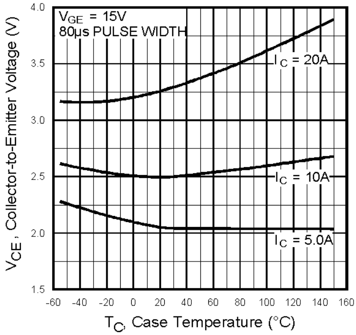


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

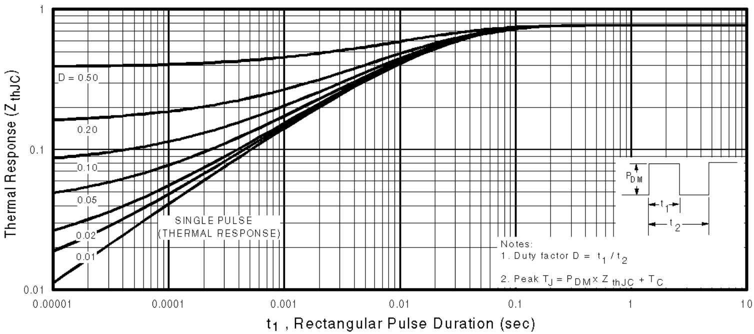


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

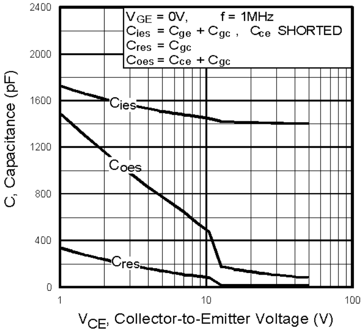


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

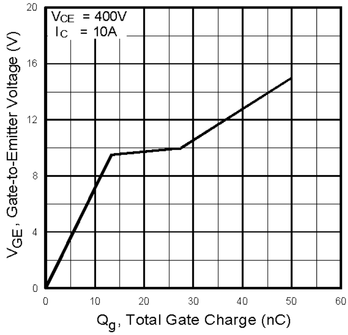


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

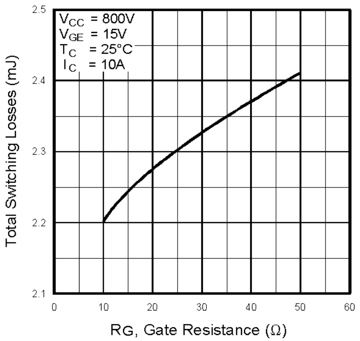


Fig. 9 - Typical Switching Losses vs. Gate Resistance

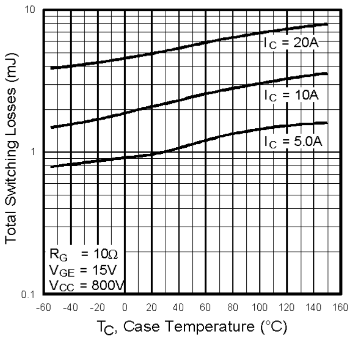


Fig. 10 - Typical Switching Losses vs. Case Temperature

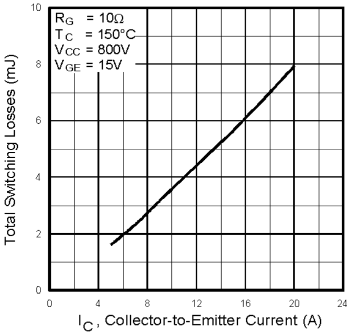


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

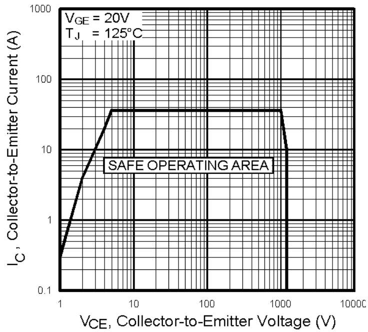


Fig. 12 - Turn-Off SOA

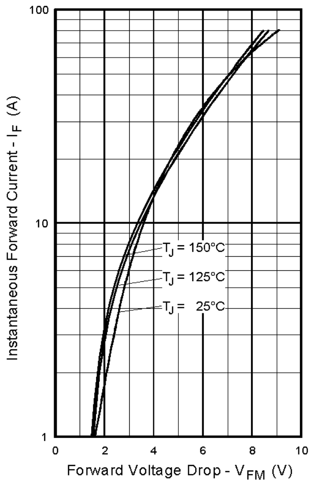


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

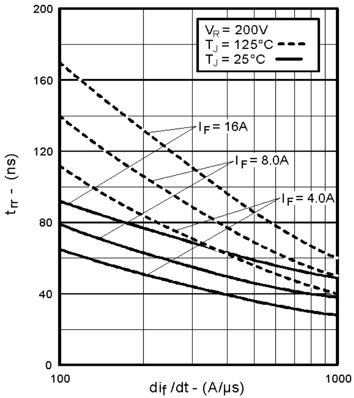


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

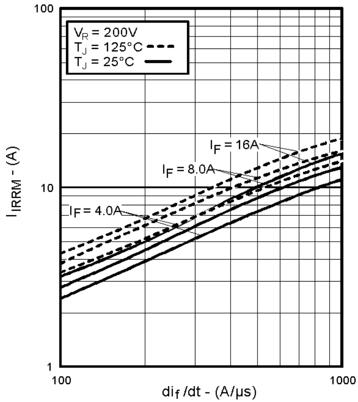


Fig. 15 - Typical Recovery Current vs. di_f/dt

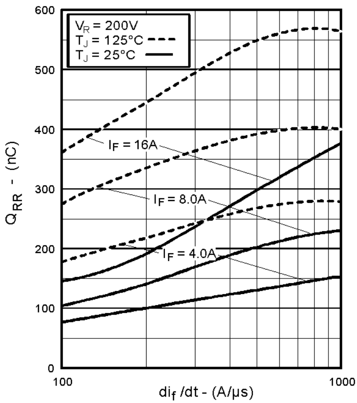


Fig. 16 - Typical Stored Charge vs. di_f/dt

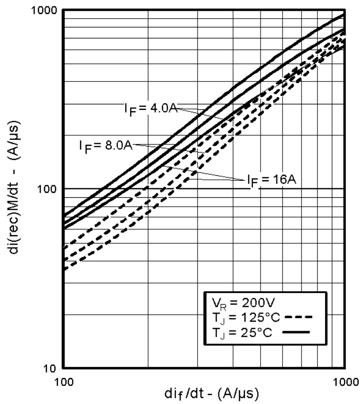


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

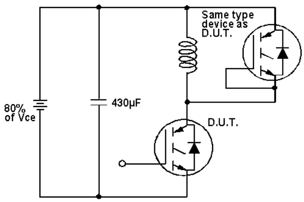


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

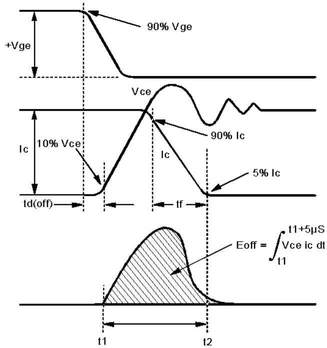


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

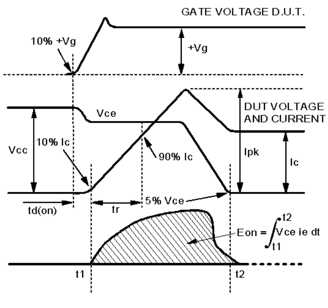


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

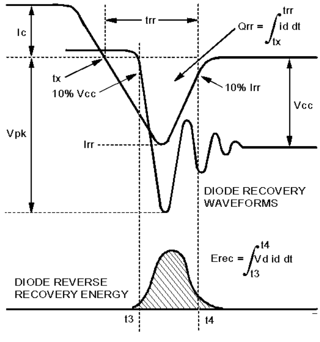


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

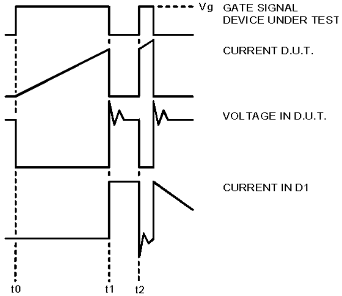


Fig. 18e - Macro Waveforms for Test Circuit of Fig. 18a

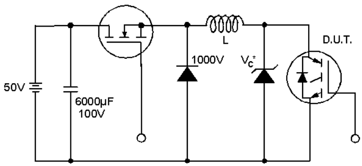


Fig. 19 - Clamped Inductive Load Test Circuit

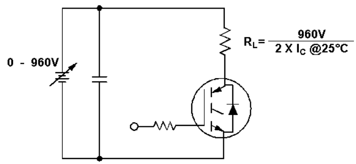
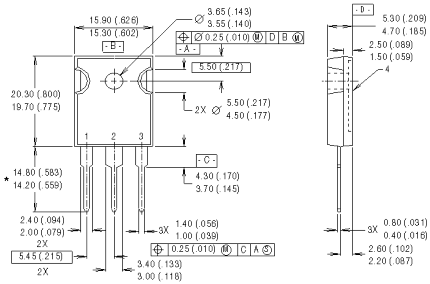


Fig. 20 - Pulsed Collector Current Test Circuit



NOTES:
1. DIMENSIONS & TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
4. CONFORMS TO JEDEC OUTLINE TO-247AC.

LEAD ASSIGNMENTS
1 - GATE
2 - COLLECTOR
3 - EMITTER
4 - COLLECTOR

* LONGER LEADED (20mm) VERSION AVAILABLE (TO-247AD) TO ORDER ADD "-E" SUFFIX TO PART NUMBER

CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)

Dimensions in Millimeters and (Inches)